

L610/PD010-35D52

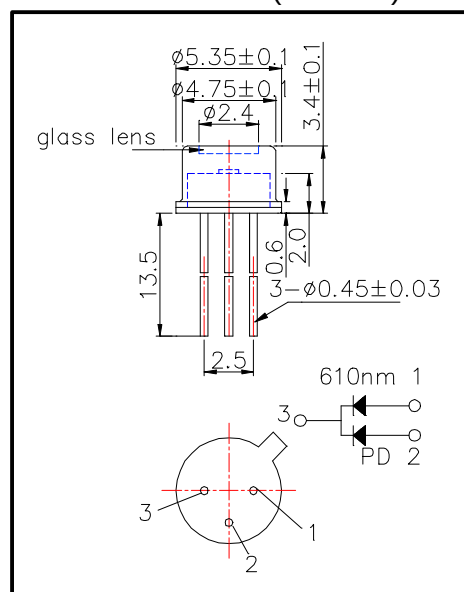
Metal can sealed PD monitoring high power LED

L610/PD010-35D52 consists of a InGaAsP LED 610nm and a Si-PD mounted into-18 stem hermetically sealed with a glass flat can, and is designed to monitor reflected light through detector for controlling its own output power

Specifications

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|---------------------|--------------------------|
| 1) Product Name | LED Lamp with PD Monitor |
| 2) Type No. | L610/PD010-35D52 |
| 3) Chip | |
| (1) Chip material | InGaAsP and Si(PIN) |
| (2) Peak wavelength | 610nm |
| 4) Package | |
| (1) Stem | f5mm TO-18 |
| (2) Lens | Metal Can (Gold Plate) |

Outer dimension(Unit:mm)



Absolute Maximum Ratings [Ta=25°C]

Device	Item	Symbol	Maximum Rated	Unit
LED	Power Dissipation	P _D	110	mW
LED	Forward Current	I _F	50	mA
LED	Pulse Forward Current	I _{FP}	300	A
LED	Reverse Voltage	V _R	5	V
PD	Reverse Voltage	V _R	100	V
	Operating Temperature	T _{OPR}	-20 ~ +85	°C
	Storage Temperature	T _{STG}	-30 ~ +95	°C
	Soldering Temperature	T _{SOL}	260	°C

‡ Soldering condition: Soldering condition must be completed within 3 seconds at 250°C

Electro-Optical Characteristics [Ta=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =20mA		2.0	2.3	V
Reverse Current	I _R	V _R =5V			10	uA
Total Radiated Power	P _O	I _F =20mA		0.8		mW
Radiant Intensity	I _E	I _F =20mA		8		mW/sr
Peak Wavelength	λ _P	I _F =20mA	600	610	620	nm
Half Width	Δλ	I _F =20mA		15		nm
Viewing Half Angle	Q _{1/2}	I _F =20mA		±55		deg.
Rise Time	t _r	I _F =20mA		100		ns
Fall Time	t _f	I _F =20mA		100		ns
Output Current	I _L	V _R =0V		65		uA
Dark Current	I _D	V _R =10V			10	nA

‡ Total Radiated Power is measured by Photodyne #500